

isc N-Channel MOSFET Transistor

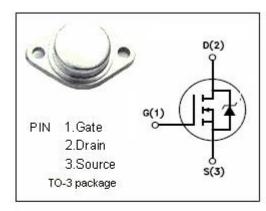
FRK250

DESCRIPTION

- 27A, 200V, RDS(on) = 0.1Ω
- Second Generation Rad Hard MOSFET Results From New Design Concepts
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

It is specially designed and processed to exhibit minimal characteristic changes to total dose and neutron exposures. Design and processing efforts are also directed to enhance survival to heavy ion (SEE) and/or dose rate (GAMMA DOT) exposure.

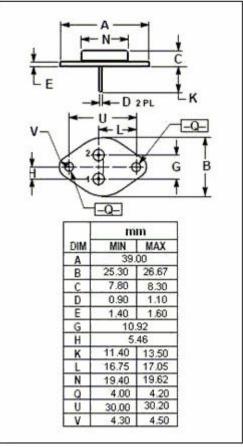


ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	ARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage (V _{GS} =0)	200	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current-continuous@ TC=37℃	27	Α
P _{tot}	Total Dissipation@TC=25℃	150	W
Tj	Max. Operating Junction Temperature	-55~150	$^{\circ}$
T _{stg}	Storage Temperature Range	-55~150	$^{\circ}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth j-c	Thermal Resistance,Junction to Case	0.83	°C/W
R _{th j-a}	Thermal Resistance,Junction to Ambient		°C/W





isc N-Channel Mosfet Transistor

FRK250

• ELECTRICAL CHARACTERISTICS (Tc=25°C)

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0; I _D = 1mA	200		V
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D = 1mA	2.0	4	V
R _{DS(ON)}	Drain-Source On-stage Resistance	V _{GS} = 10V; I _D = 17A		0.1	Ω
I _{GSS}	Gate Source Leakage Current	V _{GS} = ±20V;V _{DS} = 0		100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 200V; V _{GS} = 0		1	mA
V _{SD}	Diode Forward Voltage	I _F = 27A; V _{GS} = 0		1.8	V

NOTICE:

ISC reserves the rights to make changes of the content herein the datasheet at any time without notification. The information contained herein is presented only as a guide for the applications of our products.

ISC products are intended for usage in general electronic equipment. The products are not designed for use in equipment which require specialized quality and/or reliability, or in equipment which could have applications in hazardous environments, aerospace industry, or medical field. Please contact us if you intend our products to be used in these special applications.

ISC makes no warranty or guarantee regarding the suitability of its products for any particular purpose, nor does ISC assume any liability arising from the application or use of any products, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.